查询SN75LBC173供应商

連多邦, 专业PCB打样SN65社Bの173 QUADRUPLE LOW-POWER DIFFERENTIAL LINE RECEIVERS

SLLS170C - OCTOBER 1993 - REVISED JANUARY 2000



description

The SN65LBC173 and SN75LBC173 are monolithic quadruple differential line receivers with 3-state outputs. Both are designed to meet the requirements of the ANSI standards EIA/TIA-422-B, EIA/TIA-423-B, RS-485, and ITU Recommendations V.10 and V.11. The devices are optimized for balanced multipoint bus transmission at data rates up to and exceeding 10 million bits per second. The four receivers share two ORed enable inputs, one active when high, the other active when low.

Each receiver features high input impedance, input hysteresis for increased noise immunity, and input sensitivity of ±200 mV over a common-mode input voltage range of 12 V to −7 V. Fail-safe design ensures that if the inputs are open circuited, the output is always high. Both devices are designed using the Texas Instruments proprietary LinBiCMOS[™] technology that provides low power consumption, high switching speeds, and robustness.

These devices offer optimum performance when used with the SN75LBC172 or SN75LBC174 quadruple line drivers. The SN65LBC173 and SN75LBC173 are available in the 16-pin DIP (N) and SOIC (D) packages.

The SN65LBC173 is characterized over the industrial temperature range of –40°C to 85°C. The SN75LBC173 is characterized for operation over the commercial temperature range of 0°C to 70°C.

| FUNCTION TABLE (each receiver) | | | | | | |
|---|--------|--------|--------|--|--|--|
| DIFFERENTIAL INPUTS | ENAI | BLES | OUTPUT | | | |
| A-B | G | G | Y | | | |
| $V_{ID} \ge 0.2 V$ | H | X | H | | | |
| | X | L | H | | | |
| $-0.2 \text{ V} < \text{V}_{\text{ID}} < 0.2 \text{ V}$ | H | X | ? | | | |
| | X | L | ? | | | |
| $V_{ID} \leq -0.2 V$ | H X | X L | L | | | |
| XO | L | Н | Z | | | |
| Open Circuit | H | X | H | | | |
| | X | L | H | | | |

H = high level, L = low level, X = irrelevant, Z = high impedance (off), ? = indeterminate

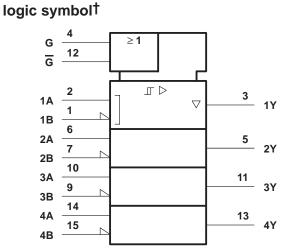


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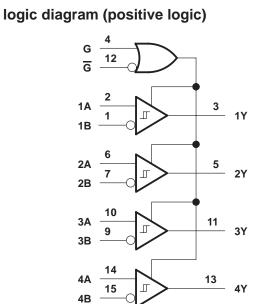
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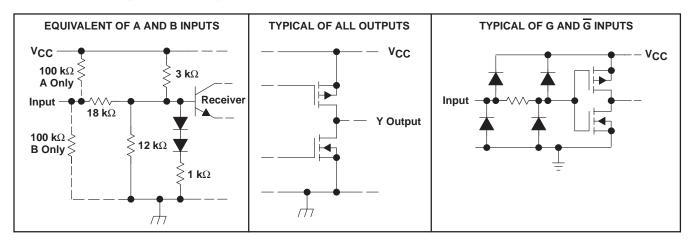
SLLS170C – OCTOBER 1993 – REVISED JANUARY 2000



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.



schematics of inputs and outputs



SLLS170C - OCTOBER 1993 - REVISED JANUARY 2000

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)[†]

| Supply voltage range, V _{CC} (see Note 1) Input voltage, V _I (A or B inputs) Differential input voltage, V _{ID} (see Note 2) Voltage range at Y, G, G | ±25 ∨ ±25 ∨ −0.3 ∨ to ∨ _{CC} + 0.5 ∨ |
|---|---|
| Continuous total dissipation | |
| SN75LBC173 | |
| Storage temperature range, T _{stg} Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds | |

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltage values are with respect to GND.

2. Differential input voltage is measured at the noninverting input with respect to the corresponding inverting input.

DISSIPATION RATING TABLE

| PACKAGE $T_A \le 25^{\circ}C$ | | DERATING FACTOR | T _A = 70°C | T _A = 85°C | |
|-------------------------------|---------|-----------------------------|-----------------------|-----------------------|--|
| POWER RATING | | ABOVE T _A = 25°C | POWER RATING | POWER RATING | |
| D | 1100 mW | 8.7 mW/°C | 708 mW | 578 mW | |
| N | 1150 mW | 9.2 mW/°C | 736 mW | 598 mW | |

recommended operating conditions

| | | MIN | NOM | MAX | UNIT |
|--|------------|-----|-----|------|------|
| Supply voltage, V _{CC} | | | 5 | 5.25 | V |
| Common-mode input voltage, VIC | | -7 | | 12 | V |
| Differential input voltage, VID | | | | ±6 | V |
| High-level input voltage, VIH | G inputs | 2 | | | V |
| Low-level input voltage, VIL | Giliputs | | | 0.8 | V |
| High-level output current, IOH | | | | -8 | mA |
| Low-level output current, IOL | | | | 16 | mA |
| Operating free-air temperature, T _A | SN65LBC173 | -40 | | 85 | - °C |
| | SN75LBC173 | 0 | | 70 | |



SLLS170C - OCTOBER 1993 - REVISED JANUARY 2000

electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

| | PARAMETER | | ТІ | EST CONDITIONS | MIN | TYP† | MAX | UNIT |
|------------------|----------------------------|----------------|----------------------------------|---|------|------|------|------------|
| VIT+ | Positive-going input three | shold voltage | $I_{O} = -8 \text{ mA}$ | | | | 0.2 | V |
| VIT- | Negative-going input three | eshold voltage | I _O = 16 mA | | -0.2 | | | V |
| V _{hys} | Hysteresis voltage (VIT. | + - VIT_) | | | | 45 | | mV |
| VIK | Enable input clamp volta | ge | l _l = – 18 mA | | | -0.9 | -1.5 | V |
| ∨он | High-level output voltage | • | V _{ID} = 200 mV, | I _{OH} = -8 mA | 3.5 | 4.5 | | V |
| VOL | Low-level output voltage | | $V_{ID} = -200 \text{ mV},$ | I _{OL} = 16 mA | | 0.3 | 0.5 | V |
| loz | High-impedance-state of | utput current | $V_{O} = 0 V \text{ to } V_{CC}$ | | | | ±20 | μΑ |
| | | | V _{IH} = 12 V, | V_{CC} = 5 V, Other inputs at 0 V | | 0.7 | 1 | mA |
| . | | A or B inputs | V _{IH} = 12 V, | $V_{CC} = 0 V$, Other inputs at 0 V | | 0.8 | 1 | mA |
| 1 | Bus input current | A OF B INPUTS | $V_{IH} = -7 V,$ | V_{CC} = 5 V, Other inputs at 0 V | | -0.5 | -0.8 | mA |
| | | | $V_{IH} = -7 V,$ | $V_{CC} = 0 V$, Other inputs at 0 V | | -0.4 | -0.8 | mA |
| ЧΗ | High-level input current | | V _{IH} = 5 V | | | | ±20 | μA |
| ΙL | Low-level input current | | V _{IL} = 0 V | | | | -20 | μA |
| los | Short-circuit output curre | ent | VO = 0 | | | -80 | -120 | mA |
| | Supply current | | Outputs enabled, | I _O = 0, V _{ID} = 5 V | | 11 | 20 | m A |
| lcc | | | Outputs disabled | | | 0.9 | 1.4 | mA |

[†] All typical values are at V_{CC} = 5 V and T_A = 25°C.

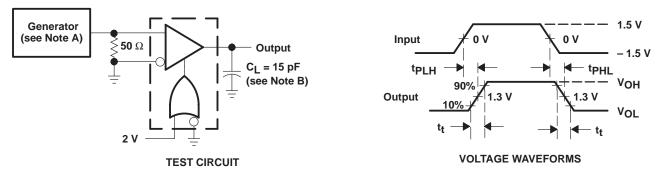
switching characteristics, V_{CC} = 5 V, C_L = 15 pF, T_A = 25°C

| PARAMETER | | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|--------------------|---|--|-----|-----|-----|------|
| ^t PHL | Propagation delay time, high- to low-level output | | 11 | 22 | 30 | ns |
| ^t PLH | Propagation delay time, low- to high-level output | $V_{ID} = -1.5$ V to 1.5 V, See Figure 1 | 11 | 22 | 30 | ns |
| ^t PZH | Output enable time to high level | See Figure 2 | | 17 | 30 | ns |
| t _{PZL} | Output enable time to low level | See Figure 3 | | 18 | 30 | ns |
| ^t PHZ | Output disable time from high level | See Figure 2 | | 35 | 45 | ns |
| t _{PLZ} | Output disable time from low level | See Figure 3 | | 25 | 40 | ns |
| ^t sk(p) | Pulse skew (t _{PHL} - t _{PLH}) | See Figure 2 | | 0.5 | 6 | ns |
| tt | Transition time | See Figure 1 | | 5 | 10 | ns |

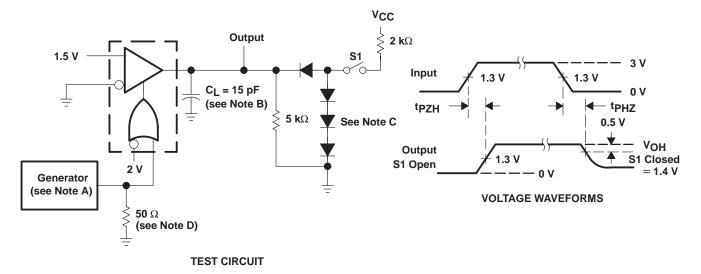


SLLS170C - OCTOBER 1993 - REVISED JANUARY 2000

PARAMETER MEASUREMENT INFORMATION





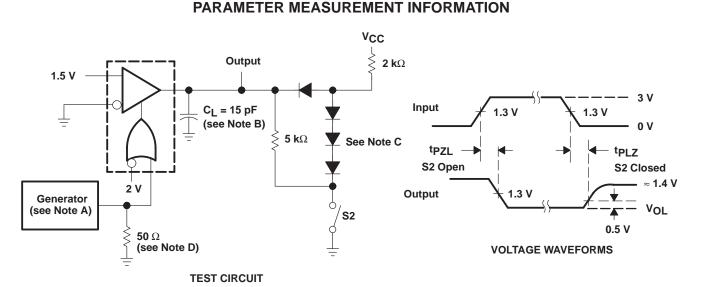


- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_{f} \le 6$ ns, $t_{f} \le 6$ ns, $Z_{O} = 50 \Omega$.
 - B. CL includes probe and jig capacitance.
 - C. All diodes are 1N916 or equivalent.
 - D. To test the active-low enable \overline{G} , ground G and apply an inverted input waveform to \overline{G} .

Figure 2. t_{PHZ} and t_{PZH} Test Circuit and Voltage Waveforms

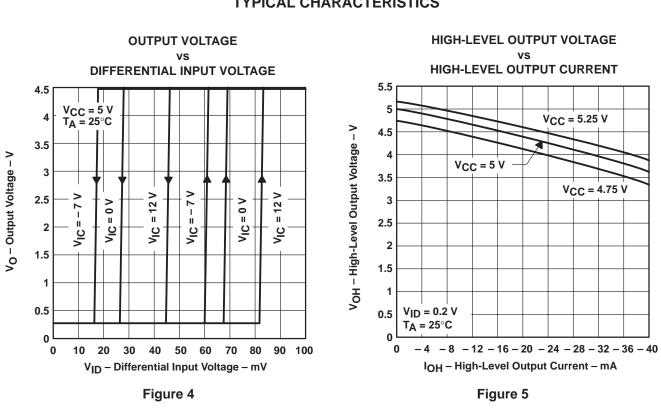


SLLS170C - OCTOBER 1993 - REVISED JANUARY 2000



- NOTES: A. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, $t_r \le 6$ ns, $t_f \le 6 \text{ ns}, Z_O = 50 \Omega.$
 - B. CL includes probe and jig capacitance.
 - C. All diodes are 1N916 or equivalent.
 - D. To test the active-low enable \overline{G} , ground G and apply an inverted input waveform to \overline{G} .

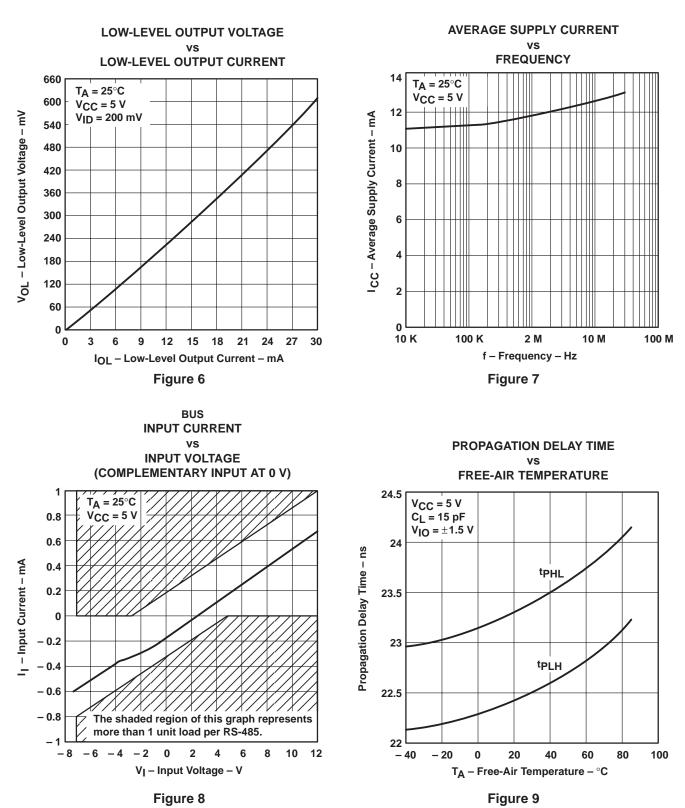
Figure 3. tPZL and tPLZ Test Circuit and Voltage Waveforms



TYPICAL CHARACTERISTICS

TEXAS

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TYPICAL CHARACTERISTICS



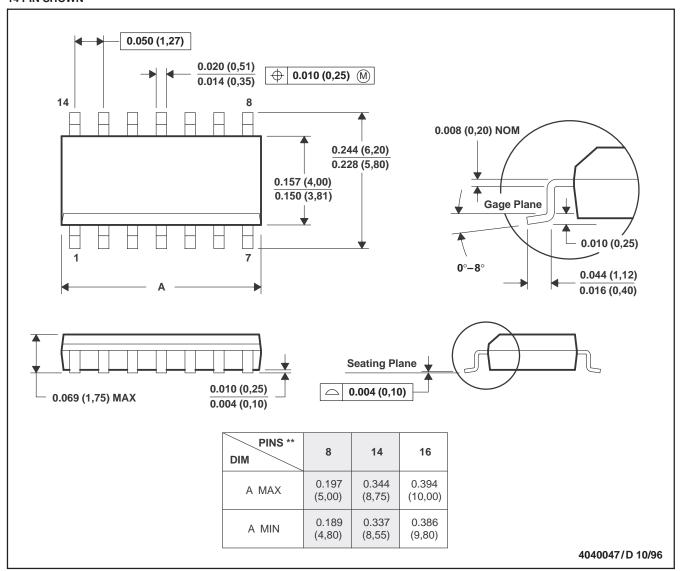
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MECHANICAL DATA

PLASTIC SMALL-OUTLINE PACKAGE

14 PIN SHOWN

D (R-PDSO-G**)



NOTES: A. All linear dimensions are in inches (millimeters).

B. This drawing is subject to change without notice.

C. Body dimensions do not include mold flash or protrusion, not to exceed 0.006 (0,15).

D. Falls within JEDEC MS-012

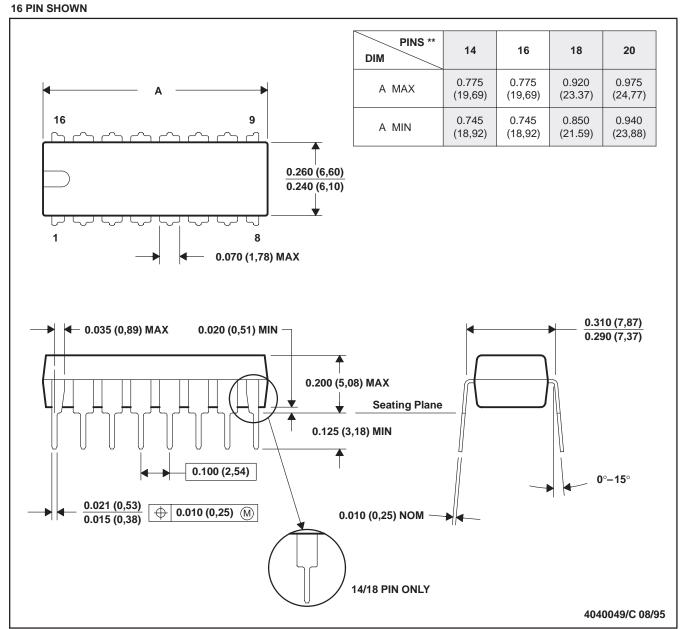


SLLS170C - OCTOBER 1993 - REVISED JANUARY 2000

MECHANICAL DATA

PLASTIC DUAL-IN-LINE PACKAGE

N (R-PDIP-T**)



NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-001 (20 pin package is shorter then MS-001.)



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